

A 12.5-MHz Bandwidth 77-dB SNDR SAR-Assisted Noise Shaping Pipeline ADC

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Abstract—This article presents a successive approximation register (SAR)-assisted noise-shaping (NS) pipeline architecture which breaks the speed bottleneck of the existing SAR or SAR-assisted-type NS analog-to-digital converters (ADCs). Rather than only for residue amplification and pipeline operation, the multiplying digital-to-analog converter (MDAC) is also reused as unity buffer and analog adder to realize the NS with error feedback (EF) structure in this design. While incorporating the proposed alternative loading capacitor (ALC) technique, an ideal first-order noise transfer function (NTF) is realized without additional feedback phase and only with a small analog circuit overhead. Unlike other NS SAR ADCs that involved amplification, the inter-stage gain attenuates the noise from the second-stage comparator, thus leading to both high speed and resolution. Fabricated in a 65-nm CMOS process, the prototype achieves a signal-to-noise-and-distortion ratio (SNDR) of 77.1 dB over 12.5-MHz bandwidth (BW) with only over-sampling ratio (OSR) of 8. Under a 1.2-V supply voltage, the ADC consumes 4.5 mW and exhibits a Scherier figure of merit (FoM) of 171.5 dB.

Index Terms—Alternative loading capacitor (ALC), analog-to-digital converter (ADC), multiplying digital-to-analog converter (MDAC) reusing, noise shaping (NS), successive approximation register (SAR)-assisted pipeline.

I. INTRODUCTION

THE Internet-of-Things (IoT) and wireless communication systems in the forthcoming technological generation require energy-efficient analog-to-digital converters (ADCs) with high dynamic range (DR), while driven from the user end, the ADC's bandwidth (BW) has to be in more than tens of megahertz [1], [2] to support large enough data throughput. The conventional successive approximation register (SAR) architecture is well known for its outstanding power efficiency, but its speed and resolution are greatly confined by the serial conversion scheme as

well as the thermal noise from the comparator and DAC mismatches [3], respectively. To relax the comparator design, the noise-shaping (NS) architecture can be hybrid within an SAR structure as first reported in [3]. It adopts an operation-transconductance-amplifier (OTA)-based active finite impulse response (FIR)-infinite impulse response (IIR) loop filter to achieve a first-order NS on both quantization and comparator noise in the SAR ADC. Nevertheless, in order to maintain a good NS efficiency and short integration time, the OTA needs to be with high gain and BW, thus leading to a power-hungry design. In [4] and [5], the proposed circuit removes the OTA by replacing the active filter in [3] with a passive switched-capacitor (SC) loop filter. Although it consumes no static power, the NS efficiency is degraded due to the signal attenuation during the passive charge sharing. Following works improve the NS efficiency and realize a high-order NS, but they still suffer from multiple input pairs of comparators leading to extra noise contribution, therefore deteriorating the NS improvement in the overall ADC signal-to-noise ratio (SNR). In [6] and [7], the dynamic amplifier is used to balance the performance between power and NS efficiency. The gain provided by the amplifier before the loop filter also suppresses the kT/C noise from the SC filters. However, the dynamic amplifier greatly suffers from process-voltage-temperature (PVT) variations that require gain calibration for a stable performance increasing the design complexity. The SAR + voltage-controlled-oscillator (VCO) hybrid structure [8] is another option to improve the resolution of the SAR ADC under low power consumption. The highly digitalized VCO is scaling friendly with the intrinsic first-order NS, while it is necessary to calibrate the tuning gain over PVT variation.

Although these designs show a promising energy efficiency to achieve high resolution, their BW is under 5 MHz for a signal-to-noise-and-distortion ratio (SNDR) > 70 dB. This is mainly due to their low-speed NS procedure, where the whole SAR conversion should be completed before the residue voltage to be processed for NS. Thus, the SAR conversion halts during the residue integration. There are also prior NS SAR ADCs achieving wide BW [3], [9], but they are only targeting low-accuracy applications. It is also worth noting that in such a range of specifications, a Nyquist ADC without NS or over-sampling already demonstrates a better efficiency [10], [11]. This implies that further research should be pursued to extend both the resolution and BW while maintaining the excellent power efficiency.

In this article, the NS technique is applied in the SAR-assisted pipeline ADC where the multiplying digital-

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to-analog converter (MDAC) is not only adopted for residue amplification but also configured as a residue adder to realize error feedback (EF) NS in the second-stage SAR ADC. The proposed alternative loading capacitor (ALC) technique ensures a unity-gain feedback for the second-stage residue voltage, resulting in a standard first-order noise transfer function (NTF) without extra active circuits, additional residue feedback, and integration phase. Incorporated with the pipeline operation, the proposed SAR-assisted NS pipeline architecture achieves higher speed over the prior single-channel NS SAR ADCs [3]–[9]. Besides, since the residue summation is accomplished by the MDAC in our EF structure, additional comparator input pair as in the feed-forward (FF) structure [3]–[6] can be avoided. Moreover, the comparator noise is further suppressed through the inter-stage gain in the pipeline architecture, and thus, the ADC can reach a high SNR with a low over-sampling ratio (OSR). The ADC prototype fabricated in 65-nm CMOS with a 1.2-V supply voltage secures 77.1-dB SNDR operating at 200 MS/s with only OSR of 8. The proposed NS architecture with an energy-efficient MDAC and accuracy-relaxed comparator consumes only 4.5 mW of power, yielding a Schreier figure of merits (FoMs) of 171.5 dB over a 12.5-MHz BW.

The organization of this article is as follows. Section II discusses the resolution and speed constraints of prior NS SAR ADCs. Section III introduces the concept of the SAR-assisted NS pipeline architecture. Section IV presents the reusing of the MDAC and ALC techniques associated with MDAC design considerations. Section V details the overall architecture and circuit implementation. Finally, we report the measured results and conclude this article in Sections VI and VII, respectively.

II. NS EFFICIENCY AND SPEED CONSTRAINTS IN SAR HYBRID NS ARCHITECTURE WITH AMPLIFIER

In prior arts, there are several hybrid ADCs that combine SAR with NS while involving amplification for the residue voltage. Such amplification leads to various effects on the overall ADC transfer function. In Section II, we will discuss their speed constraints and how their NTFs are affected by the gain of the amplifier.

A. Feed-Forward Architecture With Amplifier

Fig. 1(a) shows the block diagram of the NS SAR ADC with FF configuration assisted by an amplifier [3], [6]. Basically, it consists of an SAR ADC, an amplifier, and a loop filter. After the SAR conversion, the final residual voltage (V_{res}) is inherently ready at the DAC, which is then further sampled and passed through the loop filter to realize the desired transfer function. An additional input pair in the comparator receives the filtered residual voltage that is quantized together with the input signal in the next conversion cycle. Through the above-mentioned operations, the ADC's output (D_{out}) can be derived as

$$D_{\text{out}}(z) = V_{\text{in}} + \frac{D(z)}{D(z) + G \cdot N(z)} \cdot E_Q(z) \quad (1)$$

where E_Q is the quantization error, G is the gain of the amplifier, and $N(z)$ and $D(z)$ are the numerator and denominator in

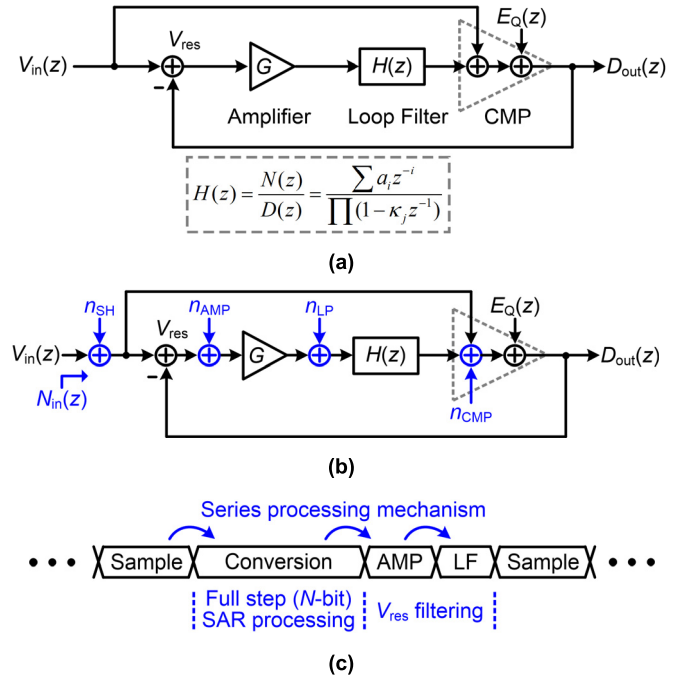


Fig. 1. (a) Block diagram, (b) noise source, and (c) timing sequence of the NS SAR ADC using the FF structure with amplifier.

the transfer function of the loop filter ($H(z)$), respectively. In the FF NS SAR ADCs without the amplifier [4], [5], the residue transmission loss due to the passive charge-sharing results in the pole of the NTF moving toward "1" ($\alpha_i < 1$) and degrades the NS ability. In [3], the OTA-based integrator in the loop filter, where the amplifier is used, prevents the signal loss during the integration process. Since the zero (κ_j) of the NTF mainly affects the noise attenuation ability at low frequency, the active integrator keeps zero close to 1 to maintain a good NS efficiency. However, it imposes a high-gain and large BW OTA for high-speed operation, while in [6], a dynamic amplifier is utilized to provide a gain of G [see Fig.1(a)] to optimize the pole of the NTF for more in-band noise attenuation through the enlarged out-of-band gain.

The complete input-referred noise expression of the FF NS SAR ADC with amplifier can be written as (2) based on Fig. 1(b)

$$N_{\text{in}} = n_{\text{SH}} + \frac{G \cdot N(z)}{D(z) + G \cdot N(z)} \cdot n_{\text{AMP}} + \frac{1}{D(z) + G \cdot N(z)} \cdot n_{\text{LP}} + \text{NTF}_Q \cdot (n_{\text{CMP}} + E_Q) \quad (2)$$

where NTF_Q represents the NTF of $E_Q(z)$ in (1). It can be clearly deducted from (2) that the comparator noise (n_{CMP}) as well as the quantization error (E_Q) are shaped. However, the amplifier's thermal noise (n_{AMP}) and the loop filter's noise (n_{LF}) are not suppressed in the band of interest, which eventually causes either a large capacitive load or a large power consumption in the amplifier or the loop filter.

Fig. 1(c) shows the timing sequence of the NS SAR ADC with the FF architecture. Based on a series processing mechanism where the integration follows the SAR conversion,

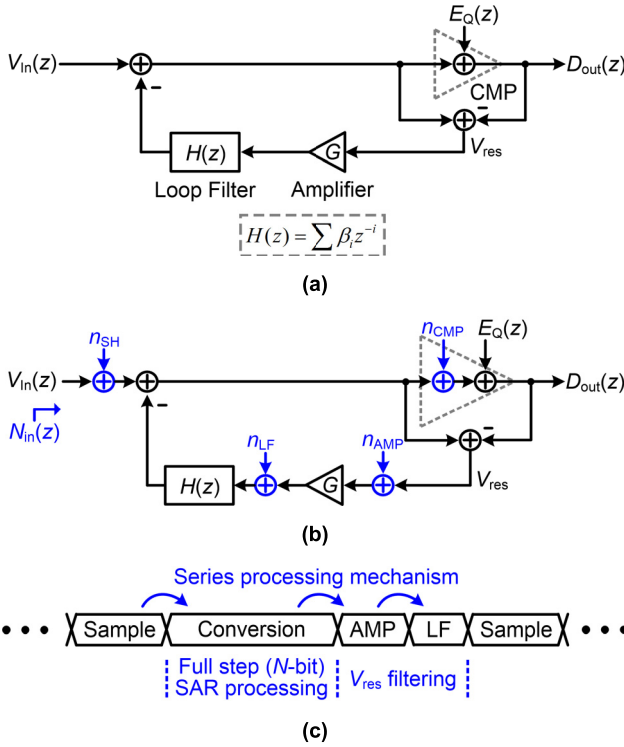


Fig. 2. (a) Block diagram, (b) noise source, and (c) timing sequence of the NS SAR ADC using error-feedback structure with amplifier.

the next sample only can be conducted after the completion of the whole SAR conversion and integration. Since N conversion cycles are needed for an N -bit SAR ADC quantization and the SAR ADC cannot release the result during the integration in [3] or amplification in [6], this setup greatly limits the speed of the ADC, especially with large N for high resolution.

B. Error Feedback Architecture With Amplifier

The EF architecture, shown in Fig. 2(a), is another commonly adopted structure for implementing SAR hybrid NS [7], [12]. It also comprises the basic SAR ADC, an amplifier, and a loop filter. After the SAR conversion, the full resolution residue is buffered to the loop filter through the amplifier with a gain of G . Different from the FF NS structure, the filtered residual voltage is added to the input signal during the next sampling period [12], and the summed voltage is subsequently quantized by the SAR ADC in the following conversion phase. The output of the ADC (D_{out}) will become

$$D_{out}(z) = V_{in}(z) + \left[1 - G \cdot \sum \beta_i z^{-i}\right] \cdot E_Q(z). \quad (3)$$

In the EF architecture, the loop filter is implemented with the combination of several delay cells, where the zeros of the NTF are related to their coefficients. Due to the passive charge sharing in the SC loop filter, the zeros are smaller than 1, resulting in a poor NS effect at low frequency. Similar to the FF architecture, the amplifier here provides gain to compensate the signal loss from the loop filter and pushes the zeroes close to the unit circle. Besides, without the extra summation pair

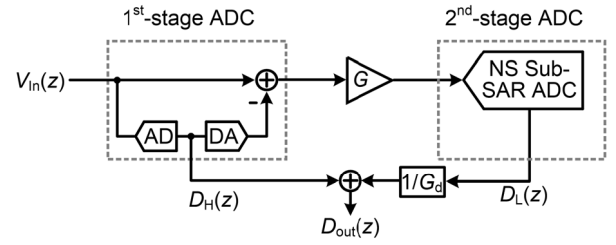


Fig. 3. Concept of the SAR-assisted NS pipeline structure.

in the comparator for FF structure that originated additional noise, the overall noise performance is also improved [7]. In [7], a further enhancement is obtained by introducing optimized zeros through the specific operation of the loop filter together with the amplifier, resulting in a notch in the NTF. Nevertheless, the location of the notch depends on G requiring gain calibration to ensure the accuracy of G and NTF.

Fig. 2(b) shows the noise source of the EF NS architecture. The input-referred transfer function of the major noise sources can be determined as

$$N_{in} = n_{SH} + \left(G \sum \beta_i z^{-i}\right) \cdot n_{AMP} + \left(\sum \beta_i z^{-i}\right) \cdot n_{LF} + NTF_Q \cdot (n_{CMP} + E_Q) \quad (4)$$

where NTF_Q represents the NTF of E_Q in (3). Generally, similar to the previously described FF architecture, the noise from the comparator also cannot be relaxed by the gain of the amplifier; besides, the amplifier has no effect on suppressing the noise from the loop filter.

The NS SAR ADC with the EF architecture is also based on a series working scheme, as shown in Fig. 2(c), which shares a similar limitation to the FF scheme in terms of speed. Although in [7], the residue is fed back to the DAC in the middle of the SAR conversion, which saves the time for residue feedback, the residue extraction and filtering process are necessary before the next ADC sampling.

III. PROPOSED SAR-ASSISTED NS PIPELINE ARCHITECTURE

As discussed in Section II, it can be concluded that there are two common issues on the prior NS SAR arts with amplifier: 1) the gain of the amplifier cannot relax the comparator noise that limits the achievable resolution, especially in an FF NS structure with an additional input pair in the comparator and 2) the full resolution conversion and integration/amplification conducted in series that limits the overall speed. To mitigate these constraints, the pipeline concept can be introduced in the NS SAR ADC, and Fig. 3 shows its block diagram. It consists of an SAR ADC in the first stage, which quantizes the coarse most significant bits (MSBs), and a pipelined NS SAR ADC in the second stage. The pipeline operation enabled by the inter-stage amplification releases the first-stage ADC to the next sampling, while the second-stage ADC determines the rest least significant bits (LSBs) conversion for complete residue extraction and filtering. This operation breaks the speed bottleneck in the existing NS SAR ADCs. In addition, the inter-stage amplification provides gain (G) to relax the

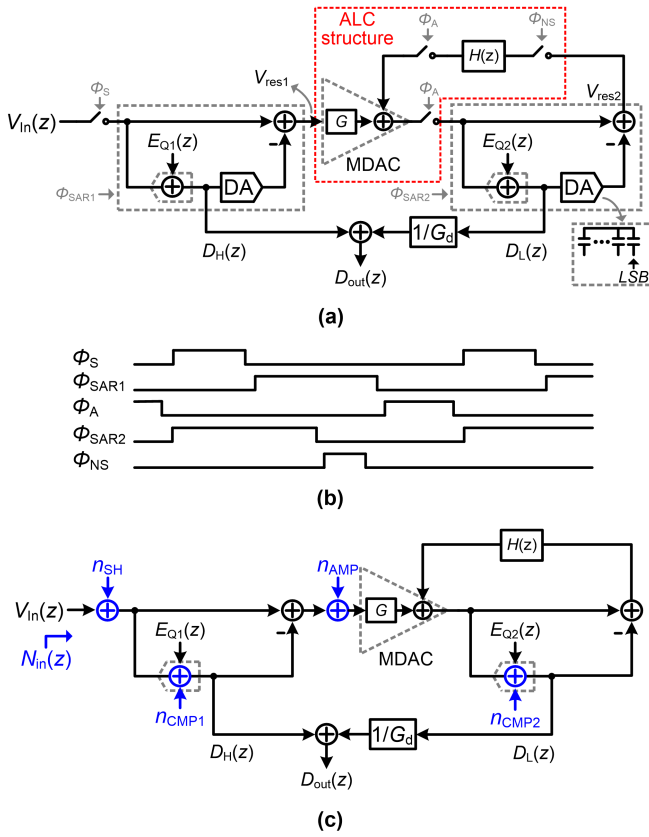


Fig. 4. (a) Block diagram, (b) timing sequence, and (c) noise source of the proposed SAR-assisted NS pipeline ADC architecture.

noise and matching requirement of the second-stage sub-ADC. Consequently, such amplification can enhance both speed and resolution from the previous NS SAR designs.

In the second stage, the NS SAR ADC can be implemented either by an FF or an EF architecture, as introduced in Section II. While the FF structure needs an extra amplifier for a good NS efficiency, the EF structure also requires an additional analog adder to sum the signal. Fortunately, in a conventional SAR-assisted pipeline architecture [10], [13], such adder is inherently available in the MDAC, which provides a convenient way to realize the EF architecture with a small hardware overhead. In this design, we reuse the residue amplifier as the analog adder to build the EF NS SAR ADC in the second stage, thus obtaining an NS pipeline structure through a small modification of the conventional SAR-assisted pipeline structure.

Fig. 4(a) shows the block diagram of the SAR-assisted NS pipeline architecture with the EF structure through the MDAC, where E_{Q1} and E_{Q2} are the quantization errors generated in the first- and second-stage SAR ADCs, respectively, and G_d is the attenuation factor for gain compensation in the digital domain. In Fig. 4(a), a feedback path containing a residue sampler (S/H), a buffer, and a loop-filter ($H(z)$) is necessary to realize the NS mechanism. Fig. 4(b) shows the timing sequence. The input signal is first sampled and quantized by the SAR ADC as the conventional operation in the SAR-assisted pipeline ADC. The second stage generates

the full-resolution residue voltage (V_{res2}) by feeding back the LSB code to the capacitive digital to analog converter (CDAC) after the completion of the conversion. Then, $H(z)$ samples and filters V_{res2} and transferred to the MDAC for residue summation during the amplification phase (Φ_A). The second-stage ADC samples the summed voltage that is further quantized in the following conversion phase. The transfer function based on this design concept can be derived as

$$D_{out}(z) = V_{in}(z) + \left(1 - \frac{G}{G_d}\right) \cdot E_{Q1}(z) + (1 - H(z)) \cdot \frac{E_{Q2}(z)}{G_d}. \quad (5)$$

It can be deduced that the quantization error from the first-stage ADC does not exist at the final ADC output, if G_d equals to G . Meanwhile, we introduce 1-bit overlapping to ensure that the conversion error from the first stage can be corrected. Eventually, the overall quantization error of the ADC only remains in the second stage that exhibits an NTF of $1 - H(z)$. Moreover, as the proposed architecture separates the SAR ADC into two stages, where the residue voltage only feeds back to the second-stage ADC, it enables the NS mechanism working in the pipeline operation. It is worth noting that there is an SAR-assisted VCO (0–1 MASH) architecture in the literature [8]; however, its first-stage SAR cannot be released during the second-stage conversion, thus posing the same speed limitation from [3], [6], and [7].

Fig. 4(c) shows the major noise sources of the proposed ADC architecture. When $G_d = G$, the input-referred NTF of the major noise sources will become

$$N_{in} = n_{SH} + n_{AMP} + (1 - H(z)) \cdot \frac{1}{G} (E_{Q2}(z) + n_{CMP2}(z)) \quad (6)$$

where n_{CMP1} and n_{CMP2} are the comparator's noises from the first- and second-stage SAR ADC, respectively. Through the proposed configuration of the SAR-assisted pipeline ADC, the second-stage quantization and comparator noise can be effectively shaped by $1 - H(z)$. Therefore, a smaller number of bits and a noisier comparator can be used in the second stage to save power when comparing it with the conventional SAR-assisted pipeline architecture. Besides, the number of unit capacitors can also be reduced in the second-stage DAC leading potentially to area saving. On the other hand, our architecture faces the same limitations as the existing NS SAR [3], [6], [7] and conventional SAR-assisted pipeline ADCs [10], [13]–[15], where the noise from the amplifier cannot be shaped. However, this design takes a further step to fully utilize the amplification for additional NS (comparing to SAR-assisted pipeline) or pipelining (comparing to NS SAR). The proposed architecture shows a great potential for high resolution or BW targets under a good power efficiency. Furthermore, similar to the conventional pipeline ADC, the mismatch error from the first-stage DAC affects the linearity of the ADC. Although the second-stage DAC mismatch error cannot be shaped, it is suppressed by the inter-stage gain G . Thus, the second-stage DAC mismatch error just has a small influence on the overall ADC's linearity.

In this design, not only the NS efficiency is guaranteed through the amplifier, reused in conventional pipeline ADC,

integrating procedures, which are the necessities in other NS SAR ADCs. According to our post-simulation results, the ALC improves the ADC's speed by 28%, while without ALC, $V_{\text{res}2}$ should be sampled by extra S/H circuit and fed back to the MDAC before the amplification phase begins.

B. Capacitor Mismatch in the ALC Structure

A potential issue from the ALC technique is the mismatch of the capacitors, which alters the inter-stage gain and the reference attenuation ratio in the second stage. Consequently, it not only leads to a noise leakage and SNR drop of the ADC but the gain error can also cause harmonic distortions. It is because the inter-stage gain and the second-stage voltage attenuation ratio change from $C_{\text{dac}1}/C_{f1}$ to $C_{\text{dac}1}/C_{f2}$ and from $C_{\text{dac}2}/(C_{f2} + C_{\text{dac}2})$ to $C_{\text{dac}2}/(C_{f1} + C_{\text{dac}2})$ in each conversion cycle, respectively, where a signal-dependent error arises. The mismatches from the inter-stage gain and the voltage attenuation ratio lead to a similar effect on the ADC, since the overall stage gain of the pipeline structure is determined by the product of these two factors. To quantify the influence of the gain mismatch on both the noise and harmonic distortion, Fig. 7 shows the simulated SNDR drop versus the variation of the inter-stage gain and the voltage attenuation ratio. It shows that the SNDR has a similar degradation when the two factors have the same variation range. According to the simulation, the mismatches of the inter-stage gain and the voltage attenuation ratio are about 0.05% and 0.2%, respectively, in our design, which leads to a less than 1-dB SNDR degradation. Therefore, the capacitor mismatch is not a concern for the ALC. It is also worth noting that the unit gain for feeding back $V_{\text{res}2}$ will not be affected by the capacitor mismatch, since its gain is not related to the capacitor ratio here.

C. MDAC Gain Accuracy Considerations

In practical implementations, the limited open-loop gain of the OTA affects the accuracy of the MDAC. While the voltage error arising in the inter-stage amplification causes noise leakage between the two pipelined stages, the non-ideal unit gain for $V_{\text{res}2}$ also results in NTF degradation. Both the effects degrade the SNR of the ADC.

When we design the open-loop gain of the OTA to be A_o , the output voltage of the MDAC based on the circuit in Fig. 6 can be written as

$$V_o = -\frac{G}{1 + \frac{1+G}{A_o}} \cdot V_{\text{res}1} + \frac{1}{1 + \frac{1}{A_o}} \cdot V_{\text{res}2}. \quad (8)$$

The flip-around MDAC structure for $V_{\text{res}2}$ amplification only consists of the OTA and $C_{f1}(C_{f2})$, which has no relation with the closed-loop gain. Thus, the $V_{\text{res}2}$ part in (8) indicates the effect of a non-ideal residue feedback caused by the finite A_o , where the unit gain is decreased to $(1 + A_o^{-1})^{-1}$. Consequently, the NTF will be altered to

$$\text{NTF} = 1 - \left(1 + \frac{1}{A_o}\right)^{-1} \cdot z^{-1}. \quad (9)$$

According to (9), Fig. 8 shows the Bode diagrams of the NTF under different values of A_o . Fig. 9(a) shows the achieved SNR

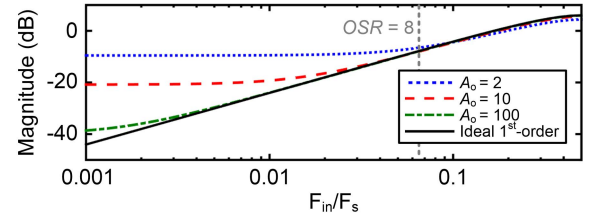


Fig. 8. Bode diagrams of the NTF under different values of A_o .

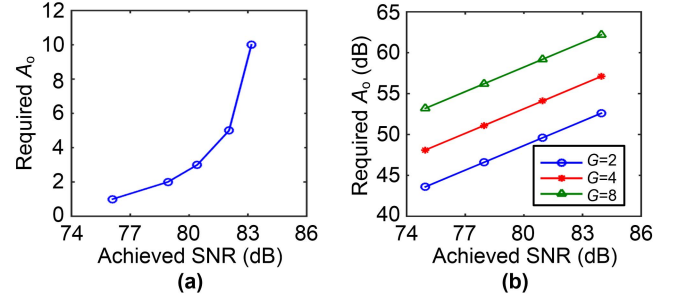


Fig. 9. Achieved SNR versus required A_o in the first-order NS pipeline architecture ($M = 6$ and $\text{OSR} = 8$) under (a) NTF degradation and (b) noise leakage.

versus the required A_o with NTF degradation due to non-unity feedback, where a (6 + 5)-bit (1-bit redundancy) pipelined structure is adopted in our design under an $\text{OSR} = 8$. It can be noticed that the SNR stays above 83 dB even with a small A_o value, which indicates that the NTF degradation due to limited A_o is not a serious concern.

It is also indicated by (8) that the non-ideal amplification of $V_{\text{res}1}$ leads to noise leakage. This error cannot be noise-shaped, but it is still over-sampled. In order to ensure the resolution, the input-referred voltage error should be less than 1/2LSB referring to the full accuracy of the converter, which is represented by

$$\frac{1}{2^M} \cdot \left(1 - \frac{1}{1 + \frac{1+G}{A_o}}\right) < \frac{1}{2} \cdot \frac{1}{2^{N-0.5\log_2\text{OSR}}} \quad (10)$$

where M and N represent the resolutions of the first stage and the ADC with NS, respectively. It is indicated by (9) that the required A_o is increased with the overall resolution (N) of the ADC, which is similar to a conventional pipeline ADC. The SNR under non-ideal A_o can be calculated according to (10), as shown in Fig. 9(b), where its degradation for small A_o due to noise leakage can be observed. In addition, a larger G value leads to a larger gain error under the same A_o , meaning that the required A_o is proportional to G for the same SNR target. Specifically, with $G = 4$ in our design, A_o has to be larger than 55 dB.

V. CIRCUIT IMPLEMENTATION AND DESIGN CONSIDERATION

A. Circuit Implementation

Fig. 10 shows the complete single-ended block diagram and the timing sequence of the proposed SAR-assisted first-order NS pipeline ADC, where a fully differential architecture is

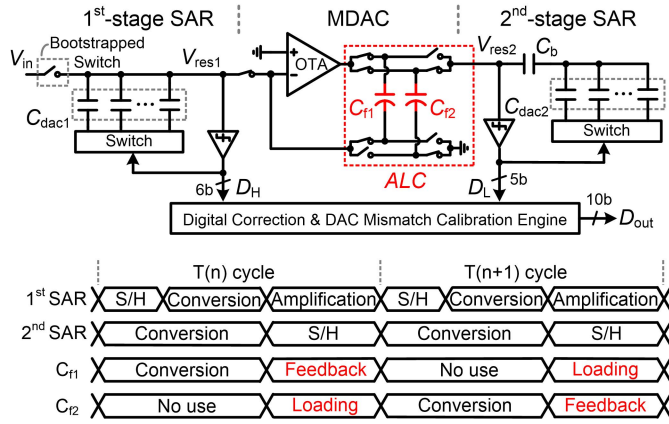


Fig. 10. Top-level schematic and timing sequence of the proposed SAR-assisted first-order NS pipeline ADC.

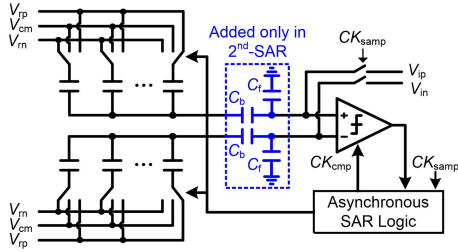


Fig. 11. Schematic of the sub-SAR ADC.

implemented in the actual design. The architecture can be defined as a (6 + 5)-bit SAR-assisted pipeline ADC with 1-bit redundancy. Both SAR ADCs adopt the V_{cm} -based switching scheme for a better linearity [16] due to its constant common-mode voltage, as shown in Fig. 11. The voltage attenuation capacitors (C_b and C_f) are only used in the second-stage ADC. The bootstrapped switch is used in the sampling circuit of the first-SAR ADC to suppress the sampling distortion. The double-tail-latch comparator [17] is adopted in both SAR ADCs. The asynchronous timing sequence is adopted in both the SAR ADCs to achieve high speed. The total capacitance of C_{dac1} and C_{f1} (C_{f2}) is 640 and 160 fF, respectively, resulting in an inter-stage gain (G) of 4. Originally, C_{dac2} should be 23 fF to achieve an attenuation factor of 1/8, resulting in a unit capacitance of 0.72 fF. However, such small unit capacitor can affect the linearity of the ADC. Consequently, a bridge capacitor C_b is added in the second stage, thus releasing the constraint of C_{dac2} which has its original size restricted by the ALC capacitors corresponding to the reference matching factor. The unit capacitance then can rise to 3 fF and C_b is set to 30 fF. The variation of C_b causes a similar effect as the reference matching error mentioned error. However, even 1% variation of C_b results in 0.7-dB SNDR drop in this design, whose effects on the performance degradation can be neglected.

Fig. 12 shows the schematic of the OTA in the MDAC. To obtain a large gain under a low supply voltage, the two-stage architecture is a good choice; however, its considerable power consumption degrades the overall efficiency of the ADC. Due to the reduced output swing of the MDAC,

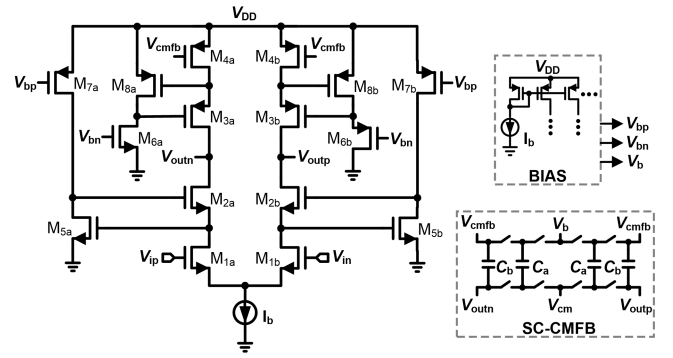


Fig. 12. Schematic of the OTA in the MDAC.

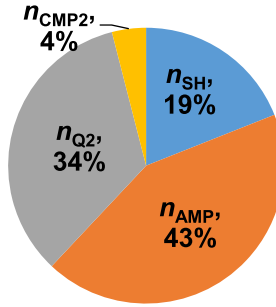


Fig. 13. Noise power breakdown.

this design employs a single-stage cascode architecture with the gain further enhanced by gain-boosting circuits (M_5 – M_8). The common-mode feedback reference (V_{cmfb}) biases M_{4a} and M_{4b} to stabilize the common-mode voltage of the OTA's output. According to the simulation results, the achieved dc gain and gain bandwidth product (GBW) of the OTA are 61 dB and 3.3 GHz, respectively, where the design margin is left for parasitic effects and PVT variations. Since the design of the closed-loop MDAC structure exhibits adequate values of open-loop gain and GBW for the OTA, the MDAC reveals high stability and accuracy, which avoids any gain calibration.

B. Noise and Linearity Design Considerations

The major noise sources of the proposed ADC structure are shown in (6), including the quantization error (E_{Q2}), the sampling kT/C noise (n_{SH}), the amplifier thermal noise (n_{AMP}), and the second-stage comparator noise (n_{CMP2}). With a target SNR around 78 dB, the quantization-limited SNR after NS and OSR of 8 is 84 dB. Moreover, $C_{dac1} = 640$ fF can satisfy the requirement of the sampling kT/C noise, which is close to -86.5 dBFS with the contribution of the OSR. On the other hand, since the noise from the amplifier cannot be shaped in this design, we intentionally assign additional power to the OTA to suppress its noise to 3.6 nV². Benefitting from the proposed architecture, n_{CMP2} is both shaped by the first-order NTF and suppressed by the inter-stage gain. Therefore, it only contributes with a very small amount to the total noise power budget, as shown in Fig. 13.

Another concern about the design is the linearity, which is mainly affected by the capacitor mismatch of the

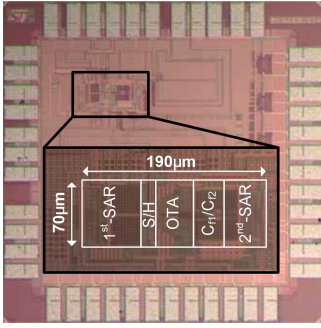


Fig. 14. Chip photograph.

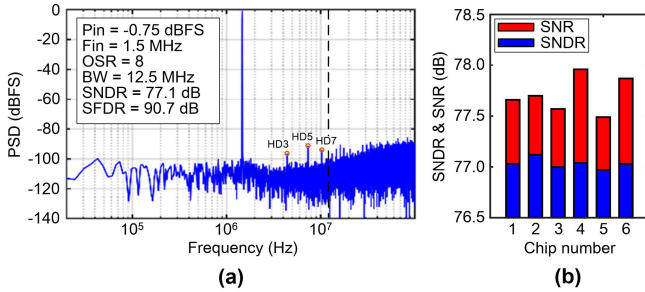


Fig. 15. (a) Measured ADC output spectrum and (b) measured results over six samples.

first-stage DAC. The mismatch error is calibrated in the foreground by estimating the actual DAC bit weight based on the least-mean-square (LMS) algorithm [19], [20]. This algorithm uses the error term between the output codes acquired with estimated bit weights and the standard codes without linearity error to update the estimated bit weights in the LMS iteration process. When the iteration finishes, the actual bit weights of the DAC capacitors are acquired and used to generate the calibrated output codes.

VI. MEASUREMENT RESULTS

Fig. 14 shows the chip micro-photograph of the ADC prototype fabricated in 65-nm CMOS with an active area of 0.014 mm². The ADC has a BW that goes up to 12.5 MHz with 200 MS/s and OSR = 8. Fig. 15(a) shows the measured 32 768-point FFT spectrum with a 1.5-MHz, -0.75-dBFS sinusoidal input signal, with the prototype reaching the peak SNDR and a spurious-free DR (SFDR) of 77.1 dB and 90.7 dB, respectively. The remaining harmonics appear in the spectrum are mainly due to the limited calibration accuracy. We measured six samples with the same testing setup, leading to the results shown in Fig. 15(b), which confirms that they have a stable SNR and SNDR with only a small variation range of less than 1 dB. Under a supply voltage of 1.2 V, the ADC consumes 4.5 mW, where the first-stage SAR, second-stage SAR, MDAC, and clock generating block account for 13%, 7%, 73%, and 7% of the total power consumption. Although the MDAC with closed-loop amplification consumes a significant amount of power, it allows our design to avoid the inter-stage gain calibration. Due to the reutilization of the MDAC with high-energy efficiency, the ADC achieves an

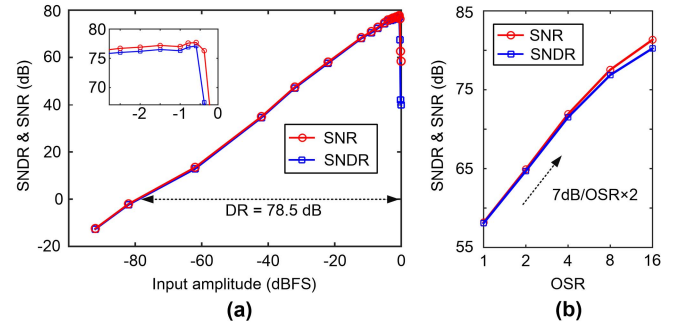


Fig. 16. Measured SNR and SNDR versus (a) input amplitude and (b) OSR.

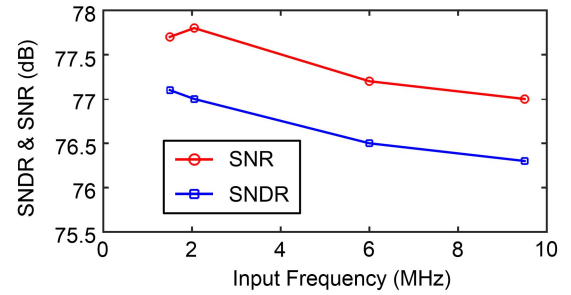


Fig. 17. Measured SNR and SNDR versus input frequency.

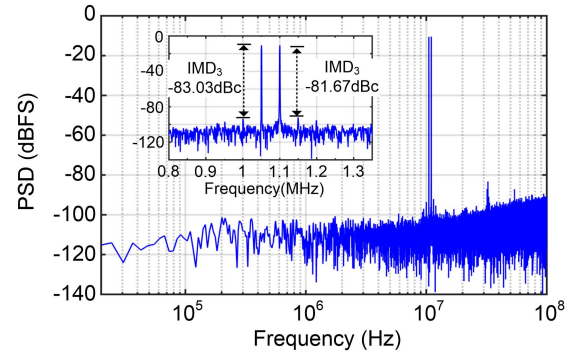


Fig. 18. Measured two-tone output spectrum.

FoMs of 171.5 dB. Fig. 16(a) shows the measured SNR and SNDR versus input amplitude, showing that the DR is 78.5 dB. Fig. 16(b) shows the measured SNR and SNDR versus OSR. Due to the noise floor, the SNR increases about 7 dB when the OSR doubles (with small OSRs), thus indicating a first-order NTF in our prototype. Fig. 17 shows the measured SNR and SNDR versus input frequency. The SNDR is above 76 dB when the input frequency increases. Fig. 18 shows the FFT spectrum of the two-tone test. The two tones are 10.5- and 11-MHz sine waves with -10-dBFS amplitude. They are close to the BW of the ADC. The measured IMD3 is -83.03 and -81.67 dBc, respectively.

Table I summarizes the performance of the ADC and compares it with the state of the arts. Our design achieves the highest BW among the single-channel NS SAR ADCs with an SNDR > 70 dB, demonstrating the effectiveness of the proposed SAR-assisted NS pipeline architecture on the enhancement of the ADC's speed at high resolution.

TABLE I
PERFORMANCE COMPARISON

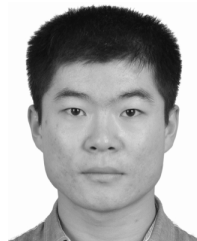
Specifications	Fredenburg, JSSC'12 [3]	Liu, ISSCC'17 [6]	Li, JSSC'18 [7]	Lin, VLSI'16 [9]	Lin, ISSCC'19 [21]	Lim, JSSC'15 [10]	Gandara, ASSCC'17 [14]	This work
Architecture	NS SAR	NS SAR	NS SAR	PNS SAR	PNS SAR	SAR Pipeline	SAR Pipeline	NS Pipeline
Technology (nm)	65	28	40	14	14	65	130	65
Supply (V)	1.2	1	1.1	1	0.9	1.2	1.2	1.2
Fs (MS/s)	90	132	10	300	320	50	10	200
BW (MHz)	11	5	0.625	25	40	25	5	12.5
SNDR (dB)	62	79.7	79	69.1	66.6	70.9	67.3	77.1
Power (mW)	0.806	0.46	0.084	2.4	1.25	1.0	0.17	4.5
FoMs (dB)	163.0	180.1	178.0	169.0	171.7	174.9	172.0	171.5
Area (mm ²)	0.03	0.0049	0.024	0.0043	0.0021	0.054	0.14	0.014

VII. CONCLUSION

This article discussed in detail the speed and resolution constraints of prior NS SAR ADCs and presented a SAR-assisted NS pipeline hybrid architecture. The proposed NS pipeline structure enables a parallel working sequence and the ALC technique avoids extra residue feedback and integration phases, which enhances the conversion speed. The noise requirement in the comparator and loop filter are relaxed due to both the EF NS structure and the inter-stage gain from the MDAC. Measurement results demonstrate that the OTA-based MDAC is of high stability without gain calibration. The ADC prototype draws 4.5-mW power from a 1.2-V supply at a BW of 12.5 MHz and exhibits 77.1-dB SNDR with only OSR of 8.

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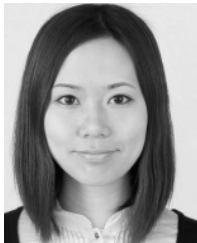
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